

N-Channel 40-V (D-S), 175°C MOSFET

PRODUCT SUMMARY

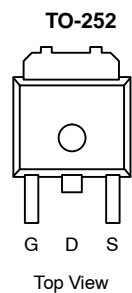
$V_{(BR)DSS}$ (V)	$r_{DS(on)}$ (Ω)	I_D (A) ^c	Q_g (Typ)
40	0.006 @ $V_{GS} = 10$ V	109	95

FEATURES

- TrenchFET® Power MOSFETS
- 175°C Junction Temperature
- High Threshold Voltage At High Temperature

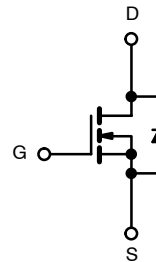
APPLICATIONS

- Automotive Such As:
 - High-Side Switch
 - Motor Drives
 - 12-V Battery



Drain Connected to Tab

Ordering Information: SUD50N04-06H—E3



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ UNLESS OTHERWISE NOTED)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	40	V
Gate-Source Voltage	V_{GS}	± 20	
Continuous Drain Current ($T_J = 175^\circ\text{C}$)	I_D	$T_C = 25^\circ\text{C}$	109 ^c
		$T_C = 100^\circ\text{C}$	77 ^c
Pulsed Drain Current	I_{DM}	100	A
Avalanche Current (Single Pulse)	I_{AS}	50	
Repetitive Avalanche Energy (Single Pulse) ^a	E_{AS}	125	mJ
Power Dissipation	P_D	136	W
Operating Junction and Storage Temperature Range	T_J, T_{stg}	-55 to 175	$^\circ\text{C}$

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Typical	Maximum	Unit
Junction-to-Ambient ^b	R_{thJA}	$t \leq 10$ sec	15	$^\circ\text{C}/\text{W}$
		Steady State	40	
Junction-to-Case	R_{thJC}	0.85	1.1	

Notes:

- Duty cycle $\leq 1\%$.
- Surface mounted on 1" FR4 board.
- Based on maximum allowable Junction Temperature. Package limitation current is 50 A.

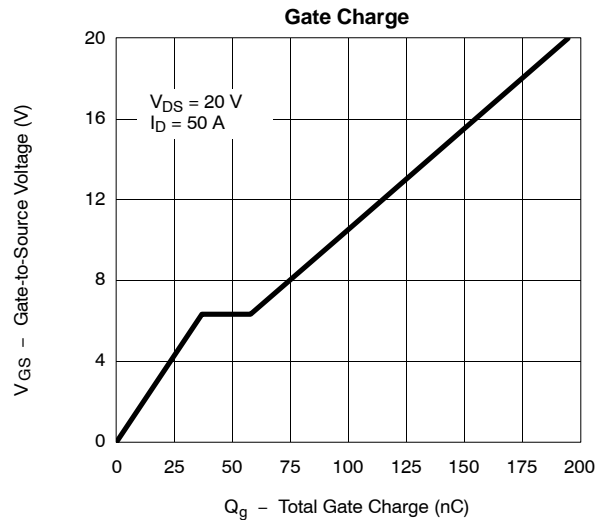
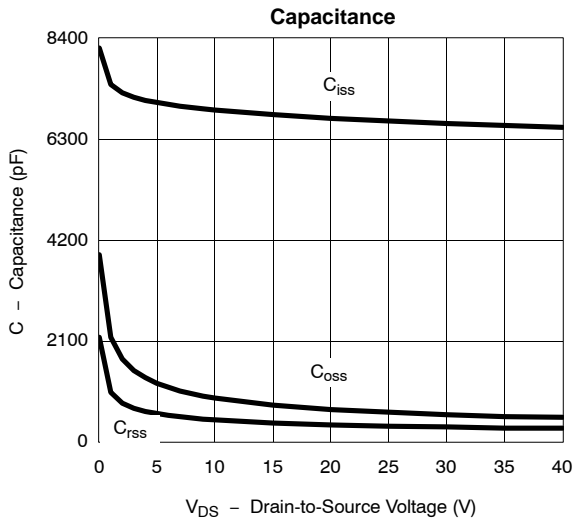
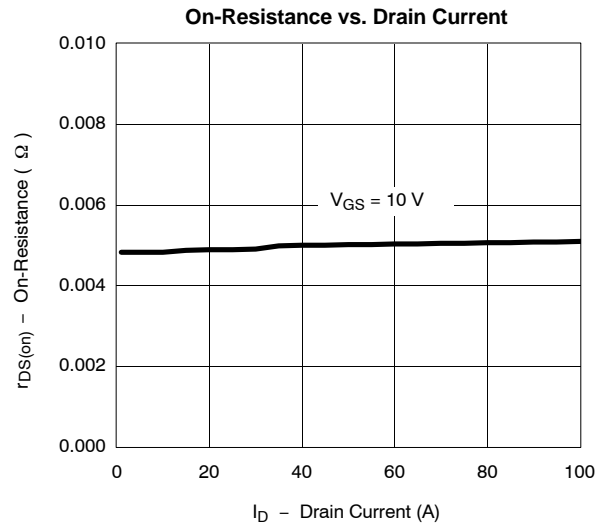
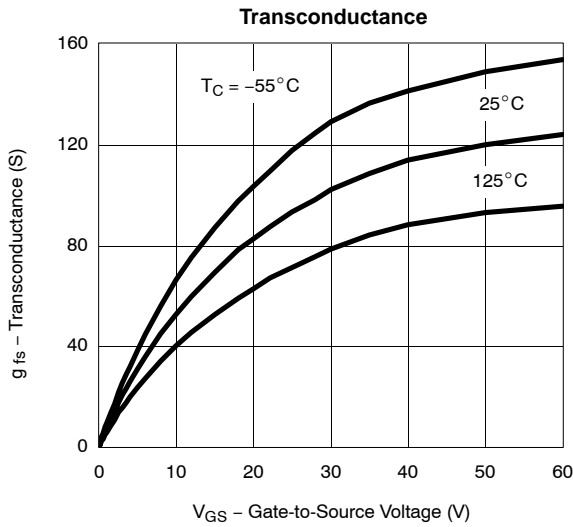
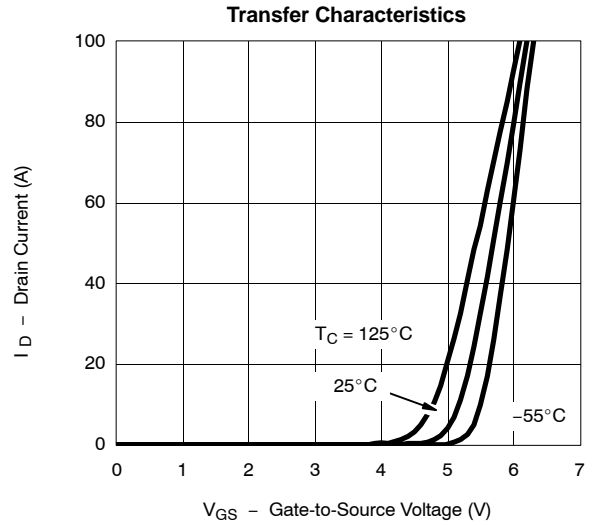
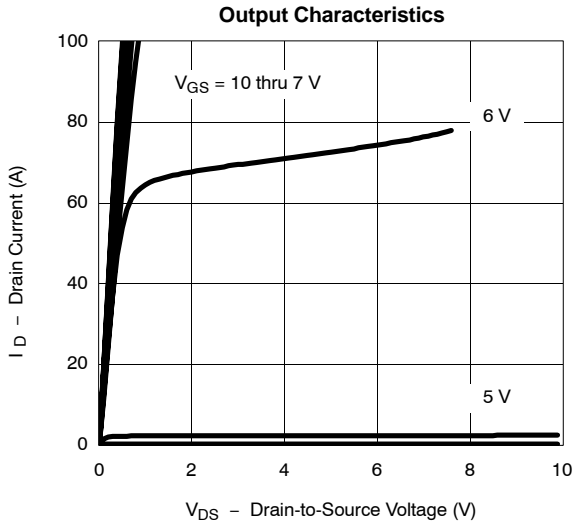
SPECIFICATIONS (T _J = 25 °C UNLESS OTHERWISE NOTED)						
Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Static						
Drain-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} = 0 V, I _D = 250 μA	40			V
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _{DS} = 250 μA	3.4		5.0	
Gate-Body Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ±20 V			±100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 40 V, V _{GS} = 0 V			1	μA
		V _{DS} = 40 V, V _{GS} = 0 V, T _J = 125 °C			50	
		V _{DS} = 40 V, V _{GS} = 0 V, T _J = 175 °C			150	
On-State Drain Current ^a	I _{D(on)}	V _{DS} = 5 V, V _{GS} = 10 V	50			A
Drain-Source On-State Resistance ^a	r _{DS(on)}	V _{GS} = 10 V, I _D = 20 A		0.0049	0.006	Ω
		V _{GS} = 10 V, I _D = 20 A, T _J = 125 °C			0.009	
		V _{GS} = 10 V, I _D = 20 A, T _J = 175 °C			0.012	
Forward Transconductance ^a	g _{fs}	V _{DS} = 15 V, I _D = 15 A	20	50		S
Dynamic^b						
Input Capacitance	C _{iss}	V _{GS} = 0 V, V _{DS} = 25 V, f = 1 MHz		6700		pF
Output Capacitance	C _{oss}			600		
Reverse Transfer Capacitance	C _{rss}			320		
Total Gate Charge ^c	Q _g	V _{DS} = 20 V, V _{GS} = 10 V, I _D = 50 A		95		nC
Gate-Source Charge ^c	Q _{gs}			37		
Gate-Drain Charge ^c	Q _{gd}			21		
Gate Resistance	R _g	f = 1.0 MHz		1.7		Ω
Turn-On Delay Time ^c	t _{d(on)}	V _{DD} = 20 V, R _L = 0.4 Ω I _D = 50 A, V _{GEN} = 10 V, R _g = 2.5 Ω		20	30	ns
Rise Time ^c	t _r			95	145	
Turn-Off Delay Time ^c	t _{d(off)}			50	75	
Fall Time ^c	t _f			12	20	
Source-Drain Ciode Ratings and Characteristics (T_C = 25 °C)^b						
Continuous Current	I _s				50	A
Pulsed Current	I _{SM}				100	
Forward Voltage ^a	V _{SD}	I _F = 30 A, V _{GS} = 0 V		0.90	1.50	V
Reverse Recovery Time	t _{rr}	I _F = 30 A, di/dt = 100 A/μs		40	60	ns

Notes:

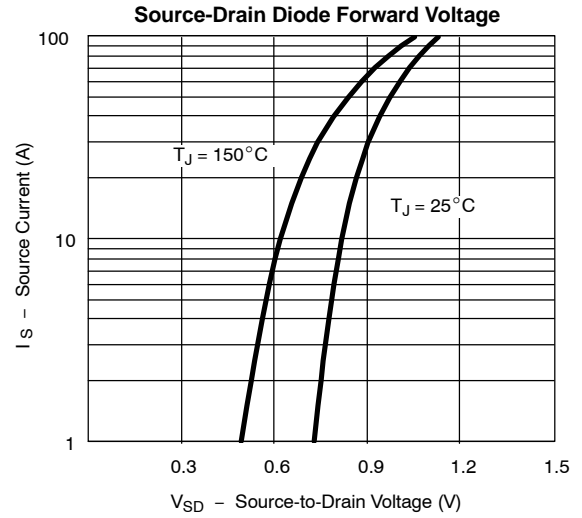
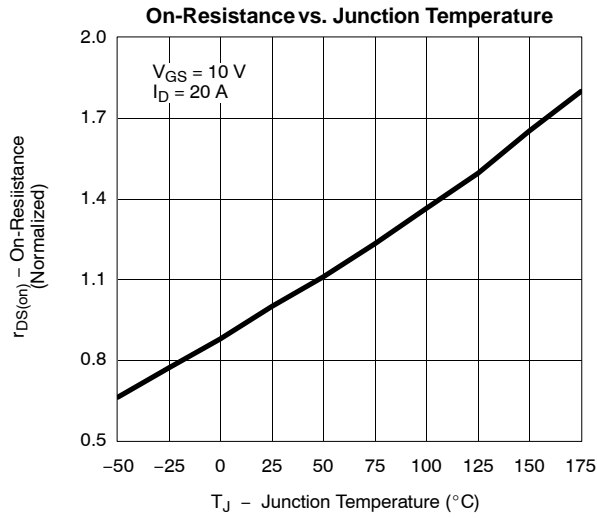
- Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2%.
- Guaranteed by design, not subject to production testing.
- Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)



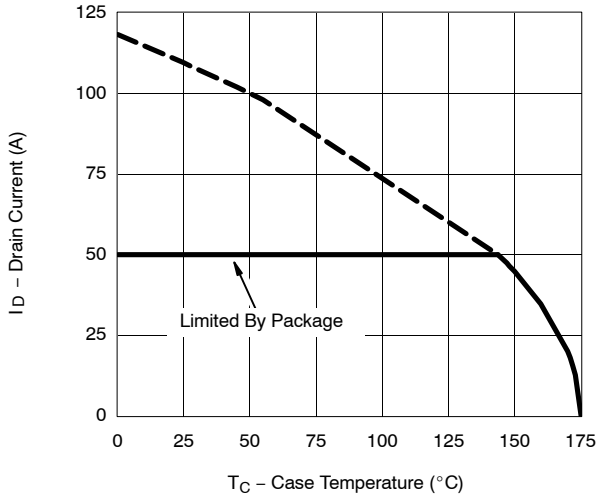
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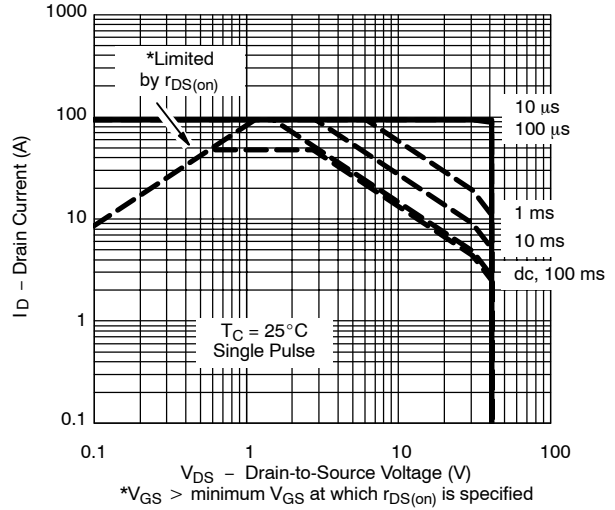


THERMAL RATINGS

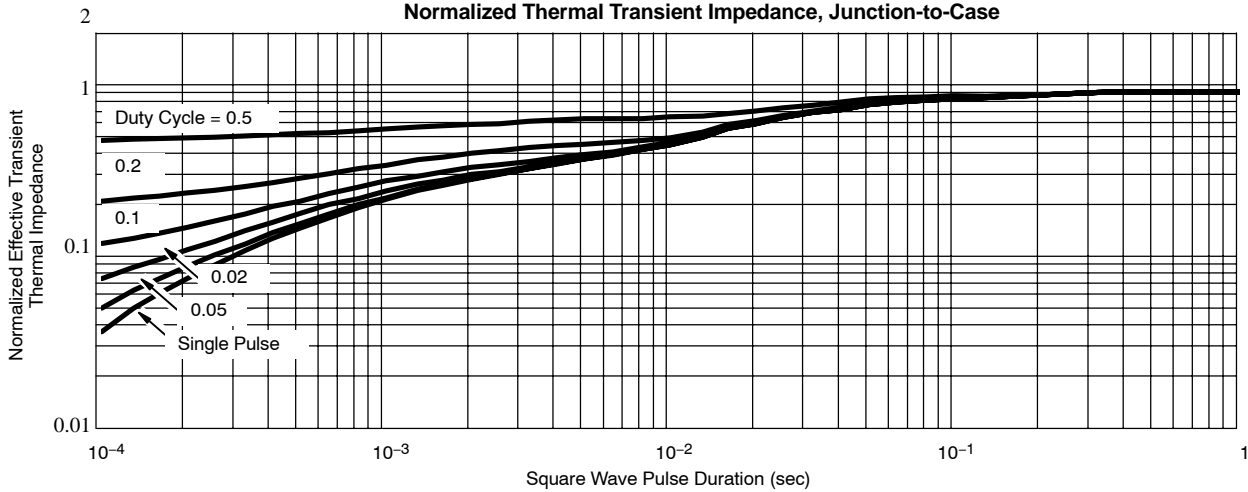
Maximum Avalanche and Drain Current vs. Case Temperature



Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Case



Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see <http://www.vishay.com/ppg?72860>.